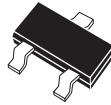


CMPD2836  
CMPD2838

SURFACE MOUNT  
DUAL, SILICON  
SWITCHING DIODES



SOT-23 CASE

**Central**<sup>TM</sup>  
**Semiconductor Corp.**

**DESCRIPTION:**

The Central Semiconductor CMPD2836 and CMPD2838 types are ultra-high speed switching diodes manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

The following configurations are available:

**CMPD2836**  
**CMPD2838**

DUAL, COMMON ANODE  
DUAL, COMMON CATHODE

**MARKING CODE: CA2**  
**MARKING CODE: CA6**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

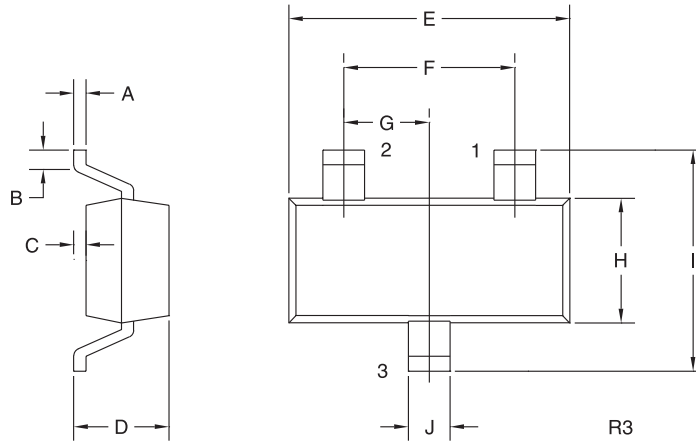
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	75	V
Average Forward Current	$I_O$	200	mA
Peak Forward Current	$I_{FM}$	300	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$BV_R$	$I_R=100\mu\text{A}$	75			V
$I_R$	$V_R=50\text{V}$			100	nA
$V_F$	$I_F=10\text{mA}$			1.0	V
$V_F$	$I_F=50\text{mA}$			1.0	V
$V_F$	$I_F=100\text{mA}$			1.2	V
$C_T$	$V_R=0, f=1.0\text{MHz}$		1.5	4.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$			4.0	ns

R5 (6-August 2003)

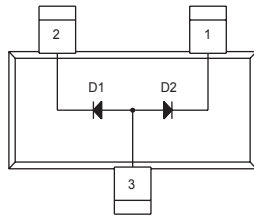
**SOT-23 CASE - MECHANICAL OUTLINE**



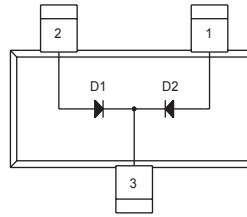
**MARKING CODE:  
CMPD2836: CA2  
CMPD2838: CA6**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)



**LEAD CODE:**  
**CMPD2836**  
1) Cathode D2  
2) Cathode D1  
3) Anode D1, Anode D2



**LEAD CODE:**  
**CMPD2838**  
1) Anode D2  
2) Anode D1  
3) Cathode D1, Cathode D2